



TO-92 Plastic-Encapsulate Transistors

2SA562 TRANSISTOR (PNP)

FEATURE

Power dissipation

$$P_{CM} : 0.5 \text{ W (Tamb=25}^\circ\text{C)}$$

Collector current

$$I_{CM} : -0.5 \text{ A}$$

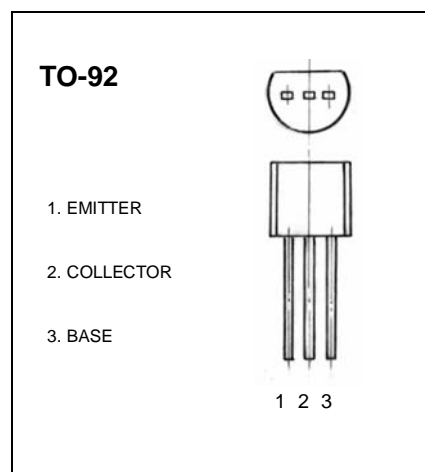
Collector-base voltage

$$V_{(BR)CBO} : -35 \text{ V}$$

Operating and storage junction temperature range

$$T_{stg} : -55^\circ\text{C to } +150^\circ\text{C}$$

$$T_J : 150^\circ\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -35\text{V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$	70		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-0.25	V
Base-emitter voltage	$V_{BE(on)}$	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE} = -6\text{V}, I_C = -20\text{mA}$ $F = 30\text{MHz}$	200			MHz

CLASSIFICATION OF h_{FE}

Rank		O	Y
Range	$h_{FE(1)}$	70-140	120-240